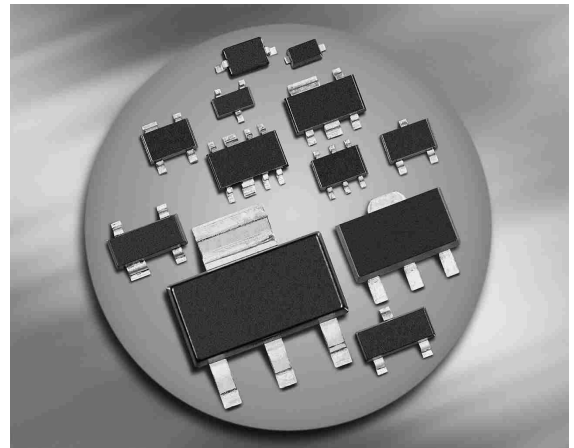
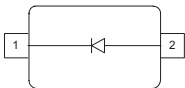


Silicon Variable Capacitance Diodes

- Frequency range up to 2 GHz
- Special design for use in TV-sat indoor unit


BB831


Type	Package	Configuration	L_S (nH)	Marking
BB831	SOD323	single	1.8	white T

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Peak reverse voltage ($R \geq 5\text{k}\Omega$)	V_{RM}	35	
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ... 125	°C
Storage temperature	T_{stg}	-55 ... 150	

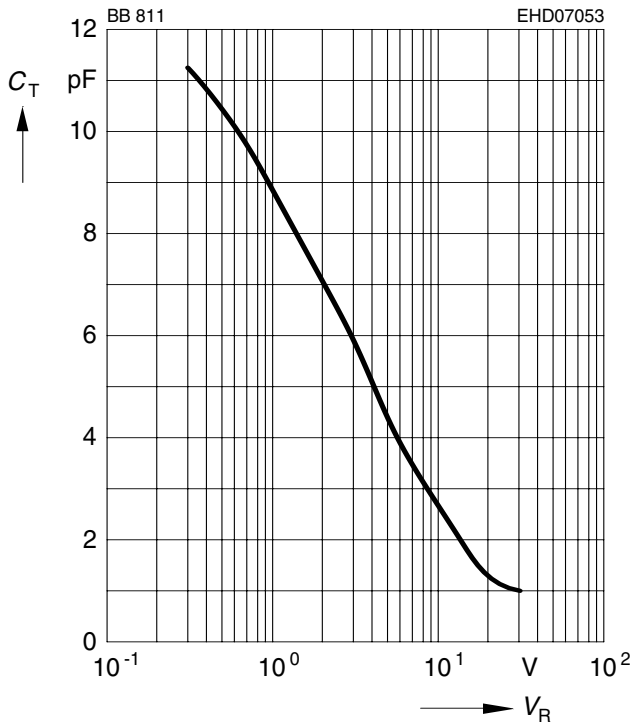
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current $V_R = 30\text{ V}$ $V_R = 30\text{ V}, T_A = 85^\circ\text{C}$	I_R	- -	- -	20 500	nA
AC Characteristics					
Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$ $V_R = 28\text{ V}, f = 1\text{ MHz}$	C_T	7.8 0.85	8.8 1.02	9.8 1.2	pF
Capacitance ratio $V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$	C_{T1}/C_{T28}	7.8	8.6	9.5	
Capacitance matching ¹⁾ $V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$	$\Delta C_T/C_T$	-	-	3	%
Series resistance $V_R = 1\text{ V}, f = 100\text{ MHz}$	r_S	-	1	-	Ω

¹For details please refer to Application Note 047.

Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$



Temperature coefficient of the diode

capacitance $T_{CC} = f(V_R)$

